

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	11.7 9.3	A
	t<10s	T _A = +25°C T _A = +70°C	I _D	14.2 11.4	A
Continuous Drain Current (Note 6) V _{GS} = 2.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	10.8 8.7	A
	t<10s	T _A = +25°C T _A = +70°C	I _D	13.2 10.6	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	80	A
Maximum Body Diode Continuous Current			I _S	2.5	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	18	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	17	mJ

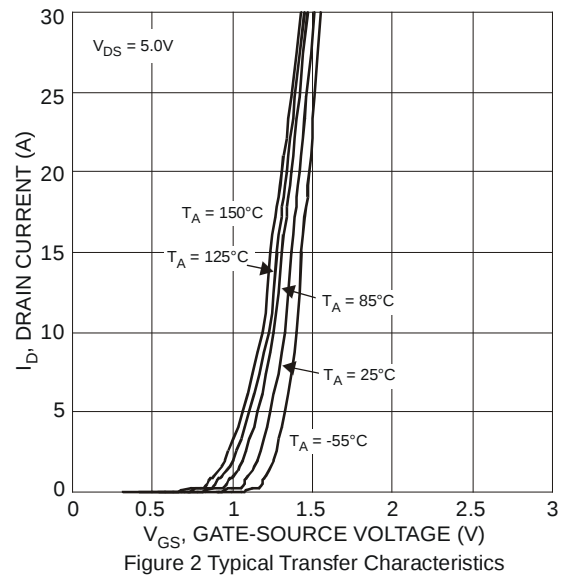
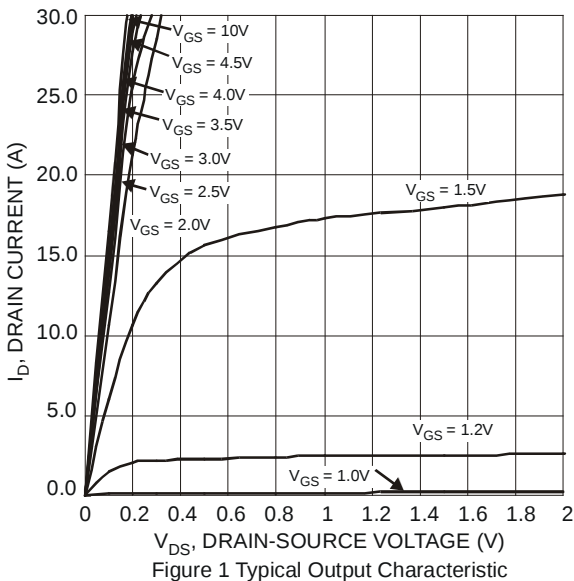
Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.61	W
	T _A = +70°C		0.39	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	209	°C/W
	t<10s		142	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.97	W
	T _A = +70°C		1.27	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	64	°C/W
	t<10s		43	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	9.8	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 16V, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	—	—	100	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	0.4	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	6.5	9.5	mΩ	V _{GS} = 4.5V, I _D = 7A
			7.5	11		V _{GS} = 2.5V, I _D = 7A
			10	20		V _{GS} = 1.8V, I _D = 5A
			15	35		V _{GS} = 1.5V, I _D = 3A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 8.5A
On State Drain Current (Note 9)	I _{D(on)}	20	—	—	A	V _{DS} ≤ 5V, V _{GS} = 4.5V
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2248	3372	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	295	443	pF	
Reverse Transfer Capacitance	C _{rss}	—	265	398	pF	
Gate Resistance	R _g	—	1.5	3	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	24	36	nC	V _{DS} = 10V, I _D = 8.5A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	56	84	nC	
Gate-Source Charge	Q _{gs}	—	3.5	6	nC	
Gate-Drain Charge	Q _{gd}	—	5.1	8	nC	
Turn-On Delay Time	t _{D(on)}	—	3.6	6	ns	V _{DS} = 10V, I _D = 8.5A V _{GS} = 4.5V, R _G = 1.8Ω
Turn-On Rise Time	t _r	—	2.6	4	ns	
Turn-Off Delay Time	t _{D(off)}	—	21.6	33	ns	
Turn-Off Fall Time	t _f	—	13.5	21	ns	I _F = 8.5A, di/dt = 210A/μs
Reverse Recovery Time	T _{rr}	—	12.8	20	ns	
Reverse Recovery Charge	Q _{rr}	—	6.9	11	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.



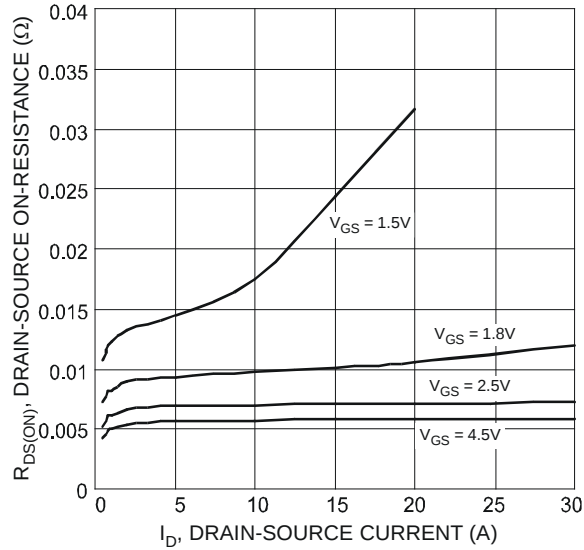


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

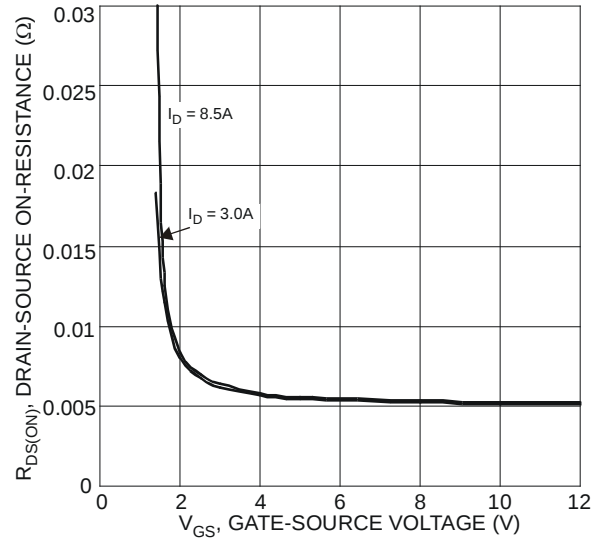


Figure 4 Typical Transfer Characteristics

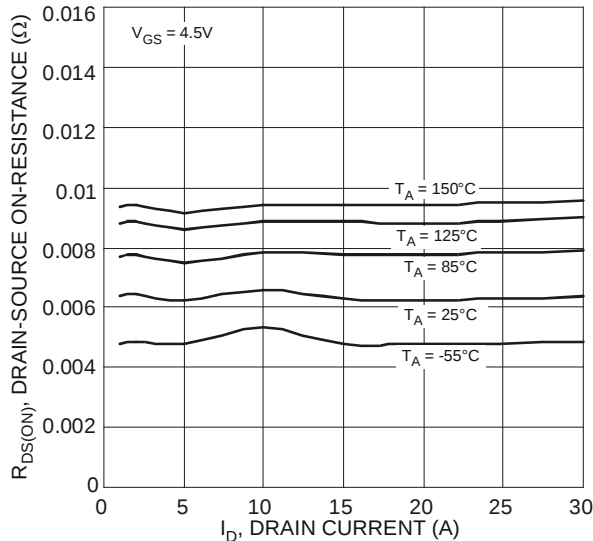


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

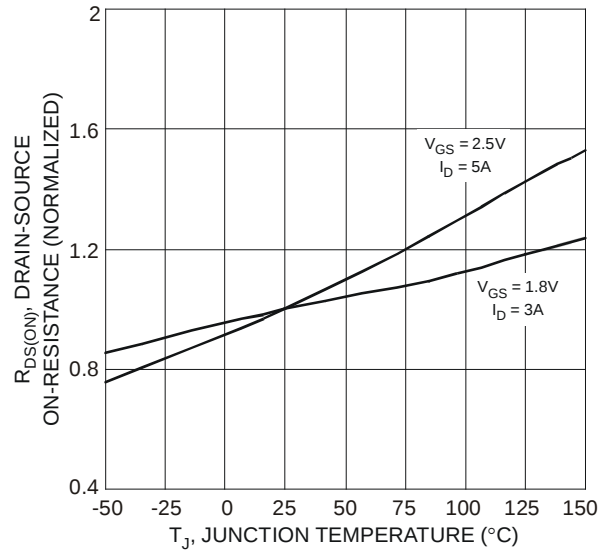


Figure 6 On-Resistance Variation with Temperature

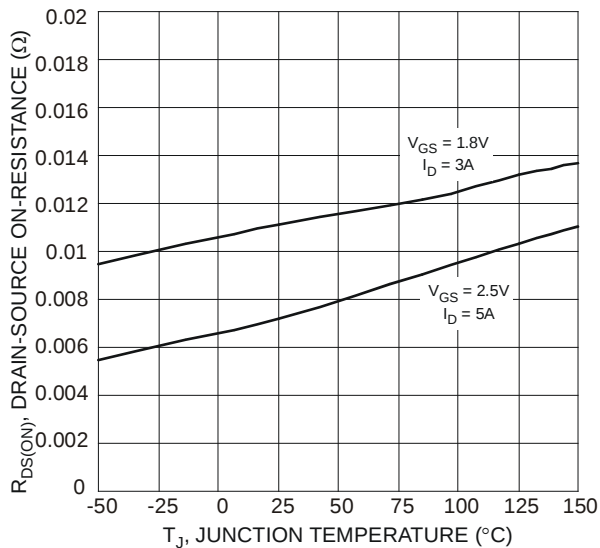


Figure 7 On-Resistance Variation with Temperature

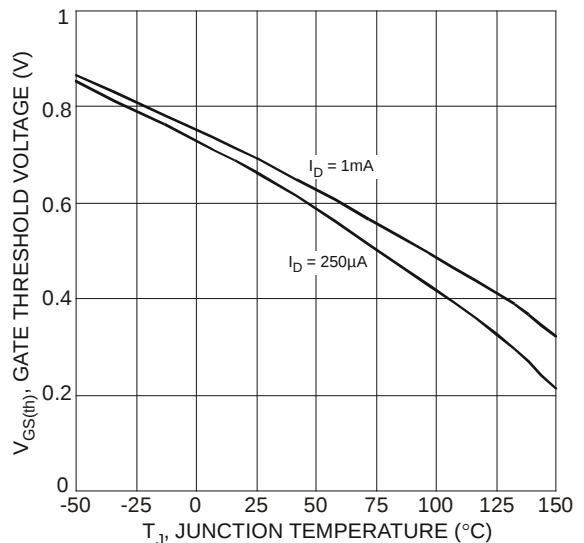
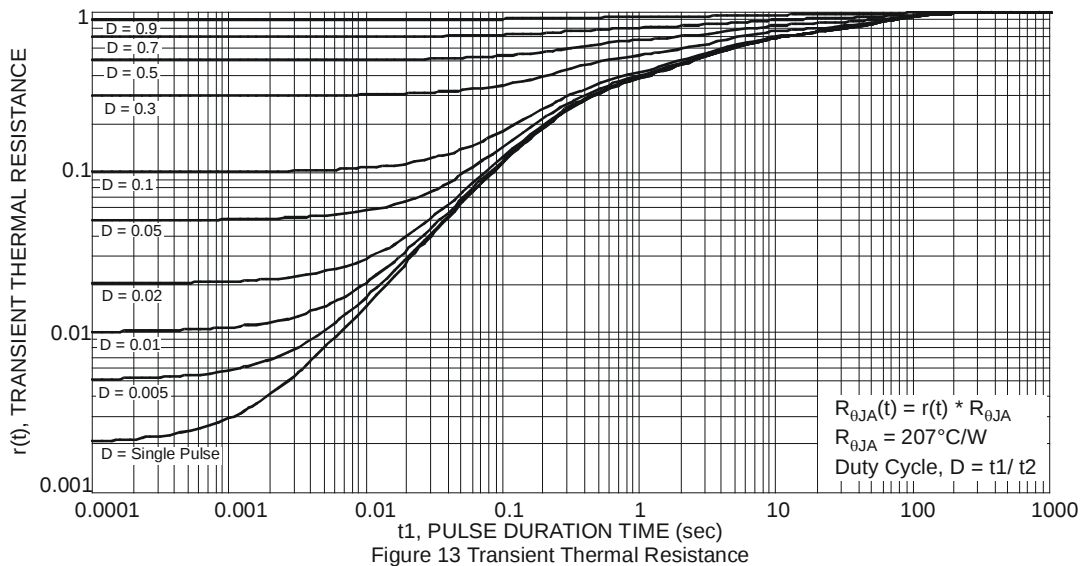
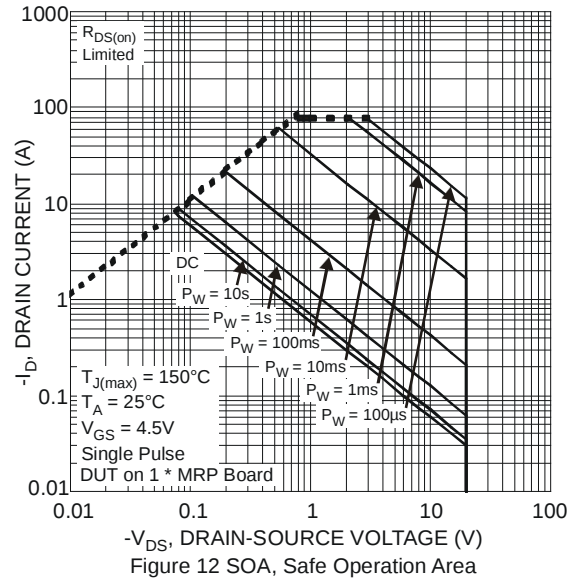
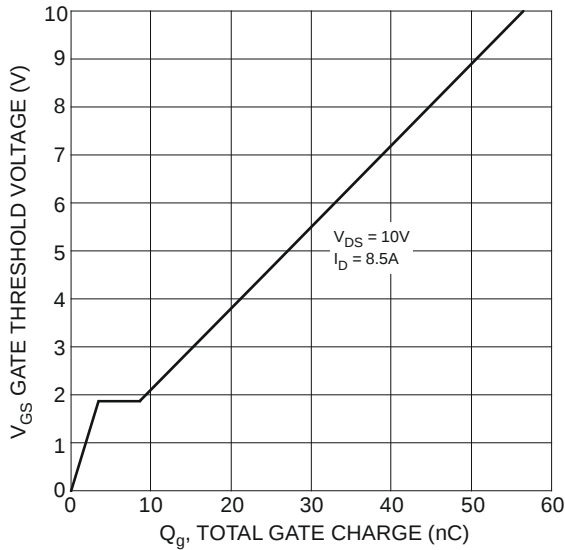
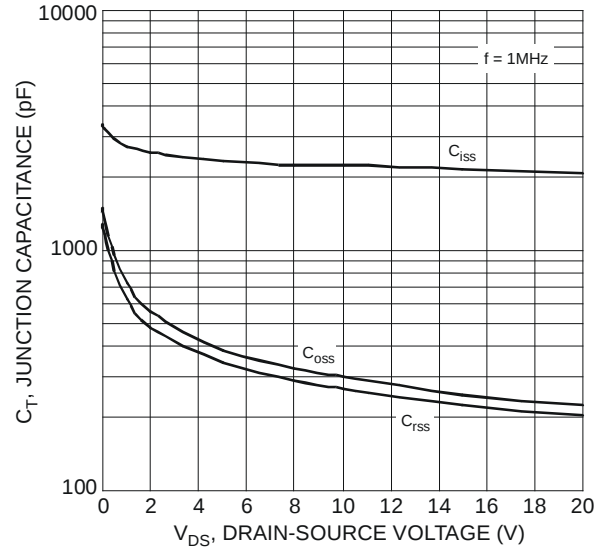
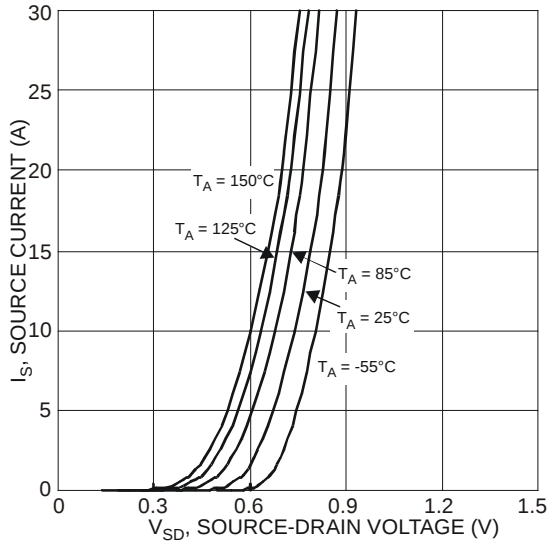
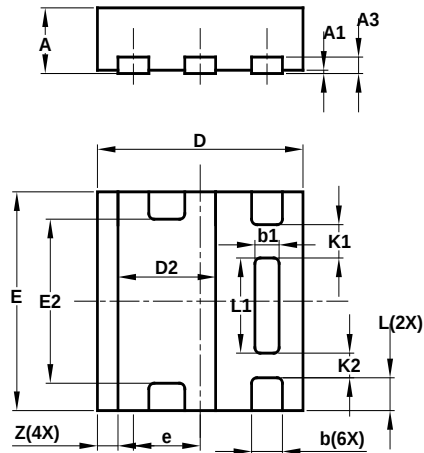


Figure 8 Gate Threshold Variation vs. Ambient Temperature



Package Outline Dimensions

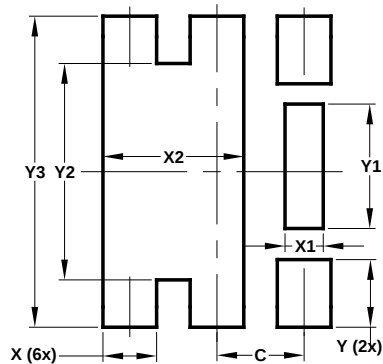
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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